



## USS4240T

Preliminary

**NPN SILICON TRANSISTOR**

### 2A, 40V NPN LOW $V_{CE(SAT)}$ TRANSISTOR

#### DESCRIPTION

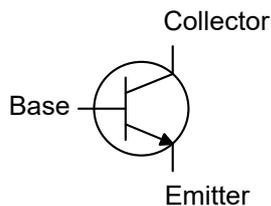
The **USS4240T** is NPN low  $V_{CE(SAT)}$  transistor in a medium power and flat lead SOT-23 Surface-Mounted Device (SMD) plastic package.

PNP complement: USS5240M.

#### FEATURES

- \* Very low collector-emitter saturation voltage  $V_{CE(SAT)}$
- \* High collector current capability  $I_C$  and  $I_{CM}$
- \* High collector current gain ( $h_{FE}$ ) at high  $I_C$
- \* High energy efficiency due to less heat generation

#### EQUIVALENT CIRCUIT



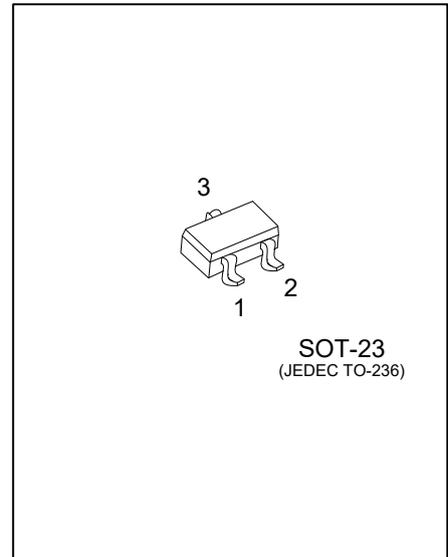
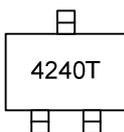
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
USS4240TL-AE3-R	USS4240TG-AE3-R	SOT-23	B	E	C	Tape Reel

Note: Pin Assignment: B: Base E: Emitter C: Collector

USS4240TG-AE3-R	(1) Packing Type	(1) R: Tape Reel
	(2) Package Type	(2) AE3: SOT-23
	(3) Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

#### MARKING



■ ABSOLUTE MAXIMUM RATING ( $T_A=25^{\circ}\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	2	A
Peak Collector Current	$I_{CM}$	3	A
Power Dissipation	$P_C$	300	mW
Junction Temperature	$T_J$	+150	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-55 ~ +150	$^{\circ}\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	417	$^{\circ}\text{C/W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS ( $T_A=25^{\circ}\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C=100\mu\text{A}$ , $I_E=0$	40			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C=1\text{mA}$ , $I_B=0$	40			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E=100\mu\text{A}$ , $I_C=0$	5			V
Collector-Base Cut-off Current	$I_{CBO}$	$V_{CB}=30\text{V}$			100	nA
Emitter-Base Cut-off Current	$I_{EBO}$	$V_{EB}=5\text{V}$			100	nA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C=2\text{A}$ , $I_B=200\text{mA}$			1.1	V
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	$V_{CE}=2\text{V}$ , $I_C=100\text{mA}$			0.75	V
DC Current Gain	$h_{FE}$	$V_{CE}=2\text{V}$ , $I_C=100\text{mA}$	350			
		$V_{CE}=2\text{V}$ , $I_C=500\text{mA}$	300			
		$V_{CE}=2\text{V}$ , $I_C=1\text{A}$	300			
		$V_{CE}=2\text{V}$ , $I_C=2\text{A}$	150			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C=100\text{mA}$ , $I_B=1\text{mA}$			70	mV
		$I_C=500\text{mA}$ , $I_B=50\text{mA}$			100	mV
		$I_C=750\text{mA}$ , $I_B=15\text{mA}$			180	mV
		$I_C=1\text{A}$ , $I_B=50\text{mA}$			180	mV
		$I_C=2\text{A}$ , $I_B=200\text{mA}$			320	mV
Transition Frequency	$f_T$	$V_{CE}=10\text{V}$ , $I_C=100\text{mA}$ , $f=100\text{MHz}$	100			MHz

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